

L Number	Hits	Search Text	DB	Time stamp
-	32262	(double or dual or multi\$4) near5 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 10:54
-	131356	fin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 10:55
-	1076015	overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:06
-	244514	mosfet or misfet or fet or (mos or mis) adj2 (transistor or device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:05
-	388909	(mosfet or misfet or fet or (mos or mis) adj2 (transistor or device)) or pmos or pmosfet or nmos or nmosfet or field adj5 (transistor or device) or igfet or ig adj fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:07
-	163236	((double or dual or multi\$4) near5 gate) or fin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:19
-	352642	spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:05
-	2988210	insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:16
-	1834033	fill\$4 or refill\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:17
-	2823565	spacer or sidewall or wall or side adj2 wall	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:25
-	194700	(insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") with (fill\$4 or refill\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:26
-	12336	(fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:27
-	608	((fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")) and ((double or dual or multi\$4) near5 gate) or fin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:28

	508	((fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")) and (((double or dual or multi\$4) near5 gate) or fin)) and (spacer or sidewall or wall or side adj2 wall)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:29
	258	((((fill\$4 or refill\$4) same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4")) and (((double or dual or multi\$4) near5 gate) or fin)) and (spacer or sidewall or wall or side adj2 wall)) and ((mosfet or misfet or fet or (mos or mis) adj2 (transistor or device)) or pmos or pmosfet or nmos or nmosfet or field adj5 (transistor or device) or igfet or ig adj fet) fin	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/25 17:29
	131548		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 10:55
	33552	((double or dual or multi\$4) near5 gate\$2) or multigate\$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 10:55
	122	fin same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:03
	131584	fin or finfet or finmos\$4 or finmis\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:04
	137	(fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:04
	353136	spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:06
	1077720	overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:06
	353136	spacer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:06
	102	((fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)) and ((overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5) or spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:07
	2992433	insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:17

-	1836583	fill\$4 or refill\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:18
-	12374	(fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:19
-	306	((fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)) and (fin or finfet or finmos\$4 or finmis\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 11:19
-	6	((fill\$4 or refill\$4) same (insulat\$4 or dielectric or oxide or dioxide or nitride or "sio.sub.2" or "sin" or "si.sub.3 n.sub.4" or "si.sub3n.sub.4") same (overhang\$4 or overhung or undercut\$5 or under adj2 cut\$5 or recess\$5)) and (fin or finfet or finmos\$4 or finmis\$4)) and (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 12:15
-	106805	(sidewall or wall or side) near10 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 12:17
-	121	((fin or finfet or finmos\$4 or finmis\$4) same (((double or dual or multi\$4) near5 gate\$2) or multigate\$2)) and (spacer or ((sidewall or wall or side) near10 gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 14:39
-	925	438/157.ccls. or 438/595.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 15:24
-	2	("6413802").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 15:25
-	2	("6252284").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/26 15:25